

Applicant: Kie Y. Ahn et al.

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO<sub>2</sub>

Docket No.: 1303.026US1  
Filed: August 30, 2001  
Examiner: David S. Blum  
Customer No.: 21186



Serial No.: 09/945535  
Due Date: September 24, 2003  
Group Art Unit: 2813  
Confirmation No.: 2681

**MS Non-Fee Amendment**

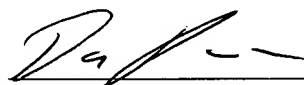
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ An Amendment and Response (11 Pages).
- ☒ Communication Concerning Co-Pending Applications (3 pgs.).

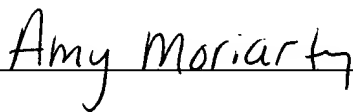
Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
Customer Number 21186

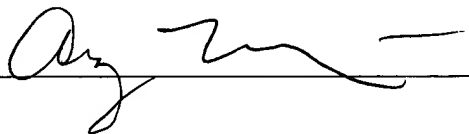
By:   
Atty: David C. Peterson  
Reg. No. 47,857

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S/N 09/945535

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: David S. Blum

Serial No.: 09/945535

Group Art Unit: 2813

Filed: August 30, 2001

Docket: 1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZRO2

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents  
P.O. Box 1450  
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Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/944981	August 30, 2001	1303.021US1	CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND Gd2O3
10/028643	December 20, 2001	1303.030US1	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS
10/052983	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/099194	March 13, 2002	1303.044US1	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAlO3 FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELETRICS

COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

Serial Number: 09/945535

Filing Date: August 30, 2001

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZRO2

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10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO <sub>3</sub> FILMS FOR GATE DIELECTRICS
10/163686	June 5, 2002	1303.059US1	Pr <sub>2</sub> O <sub>3</sub> -BASED La-oxide GATE DIELECTRICS
10/209581	July 30, 2002	1303.061US1	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO <sub>2</sub> /ZrO <sub>2</sub> FILMS AS GATE DIELECTRICS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiO <sub>x</sub> DIELECTRIC FILMS BY PLASMA OXIDATION
10/219878	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiO <sub>x</sub> DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiO <sub>n</sub> DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiO <sub>x</sub> DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN- TI-O FILMS USING TiH <sub>4</sub>
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn- Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAl <sub>x</sub> O <sub>y</sub> DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO <sub>4</sub> FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

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09/779959 February 9,  
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Respectfully submitted,

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By Applicants' Representatives,

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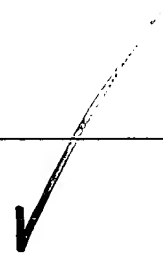
Date 9-24-03

By



David C. Peterson

Reg. No. 47,857



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Name

Amy Moriarty

Signature

